



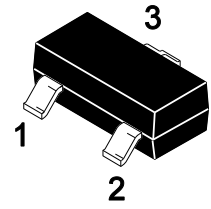
# BAW56<sup>\*</sup>

## Silicon Epitaxial Planar Switching Diode

### Features

- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

### Pin Configuration

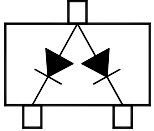


1.Cathode1 2.Cathode2  
3.Anode1、 Anode2

Marking Code : AW1

### Internal Structure

3.Anode1、 Anode2



1.Cathode1 2.Cathode2

### Electrical Characteristics (T<sub>J</sub> = 25°C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	70	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	200	mA
Non-Repetitive Peak Forward Surge Current	I <sub>FSM</sub>	2	A
Maximum Power Dissipation	P <sub>D</sub>	225	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (T<sub>J</sub> = 25°C)

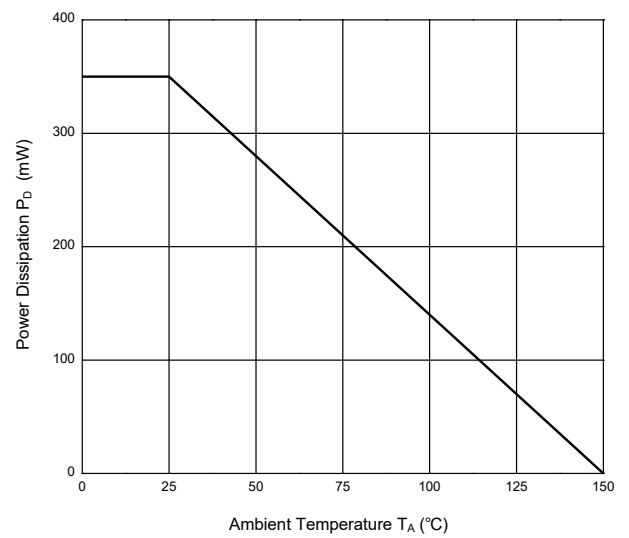
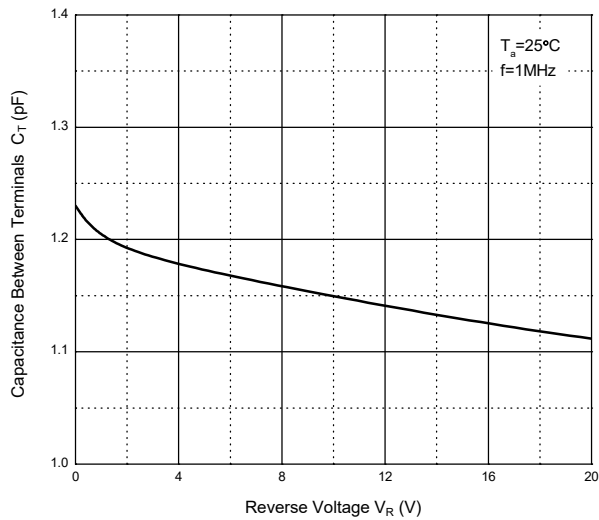
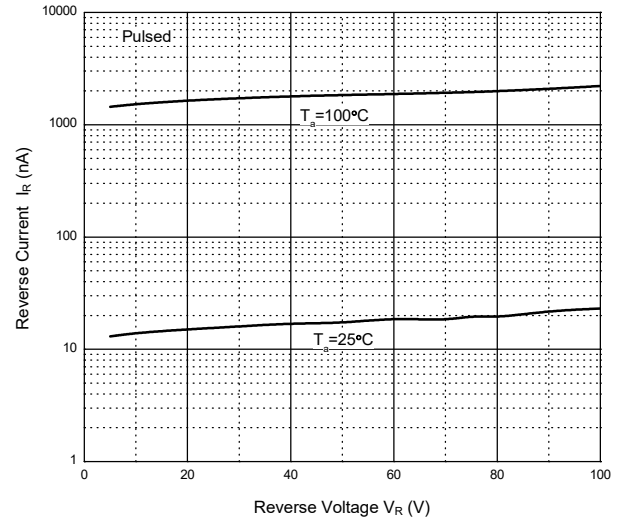
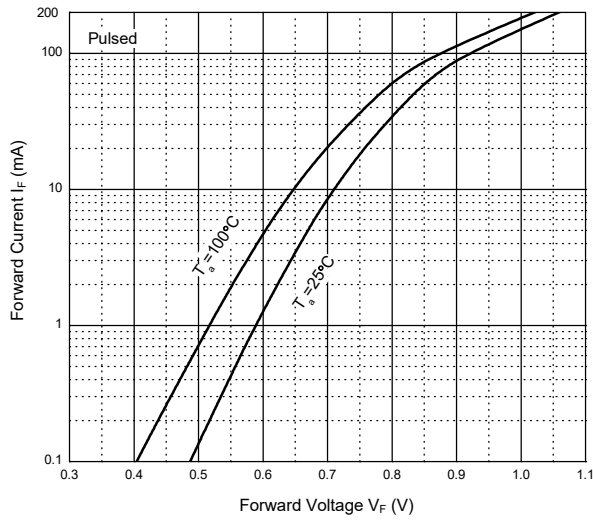
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I <sub>F</sub> = 1 mA	V <sub>F</sub>	--	0.715	V
at I <sub>F</sub> = 10 mA		--	0.855	
at I <sub>F</sub> = 50 mA		--	1	
at I <sub>F</sub> = 150 mA		--	1.25	
Reverse Breakdown Voltage at I <sub>R</sub> = 100 μA	V <sub>(BR)R</sub>	70	--	V
Reverse Current at V <sub>R</sub> = 70 V	I <sub>R</sub>	--	2.5	μA
Typical Junction Capacitance at V <sub>R</sub> = 0 V, f = 1 MHz	C <sub>j</sub>	--	1.5	pF
Maximum Reverse Recovery Time at I <sub>F</sub> = I <sub>R</sub> = 10 mA, I <sub>RR</sub> = 0.1 × I <sub>R</sub> , R <sub>L</sub> = 100Ω	T <sub>rr</sub>	--	6	nS



# BAW56<sup>®</sup>

## Silicon Epitaxial Planar Switching Diode

### Typical Characteristic Curves





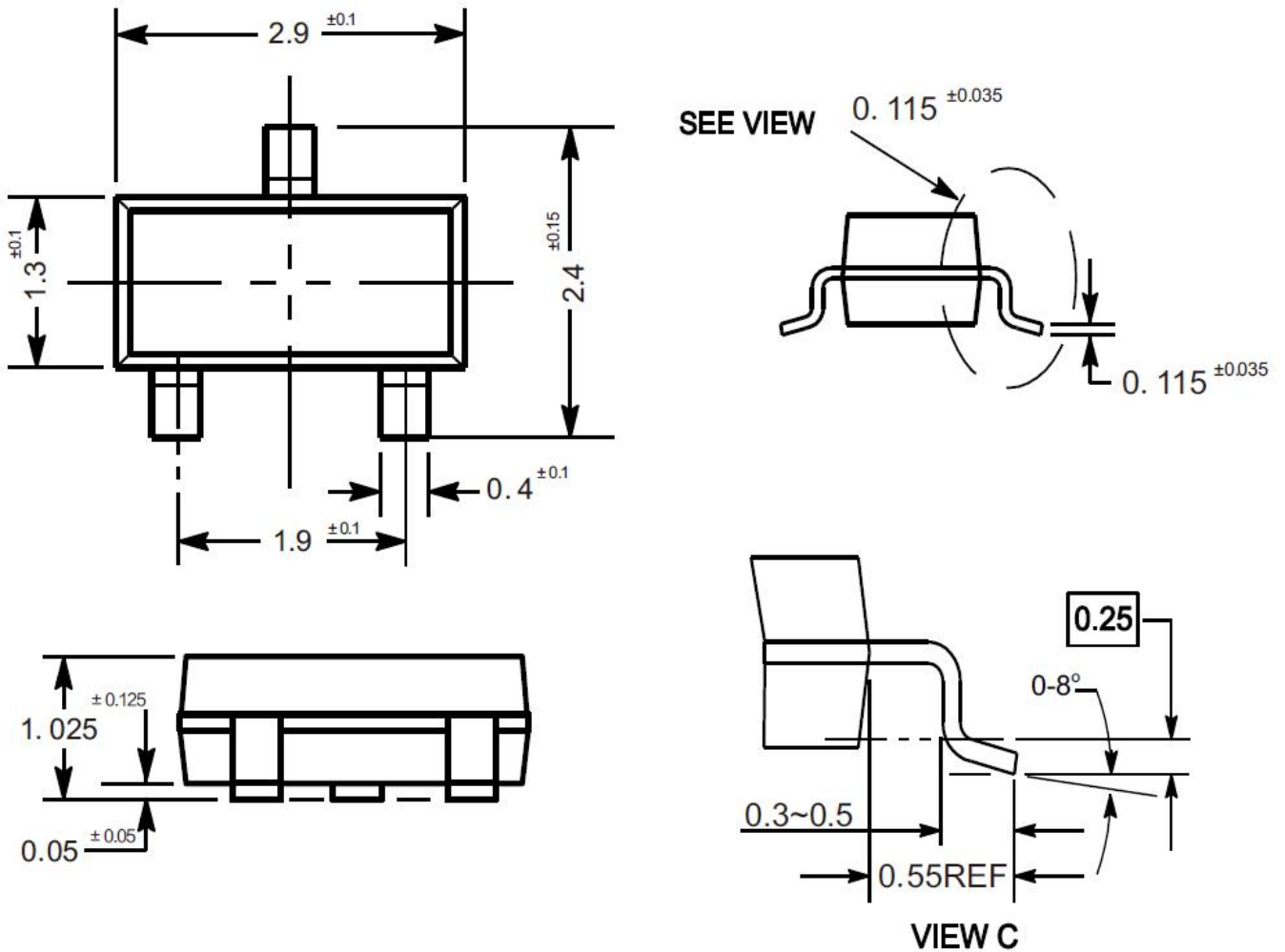
# BAW56<sup>+</sup>

## Silicon Epitaxial Planar Switching Diode

### Package Outline

SOT-23

Dimensions in mm



### Ordering Information

Device	Package	Shipping
BAW56	SOT-23	3,000PCS/Reel&7inches